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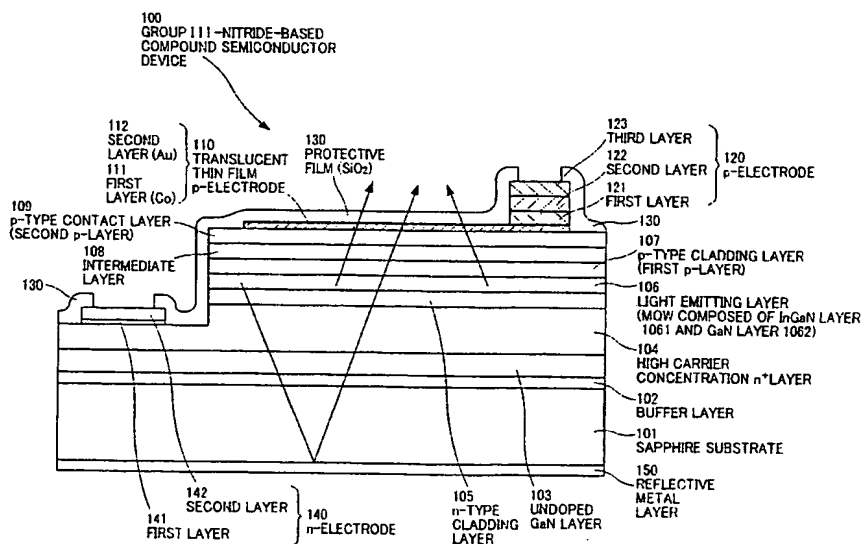
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(54) Title: **GROUP III-NITRIDE-BASED COMPOUND SEMICONDUCTOR DEVICE**



(57) Abstract: In a group III-nitride-based compound semiconductor device 100, an intermediate layer 108 is 5 provided between a p-AlGaIn layer 107 and a p-GaN layer 109, to each of which an acceptor impurity is added. On this occasion, the intermediate layer 108 is doped with a donor impurity in a concentration, by which holes generated by an acceptor impurity introduced into the intermediate layer 108 during the formation of the p-AlGaIn layer 107 are substantially compensated. As a result, the conductivity of the intermediate layer 108 becomes extremely low, and therefore the electrostatic withstand voltage of the group III-nitride-based compound semiconductor device 100 improves significantly.

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